

Cross sections of EUV PAGs: Influence of Concentration, Electron Energy, and Structure

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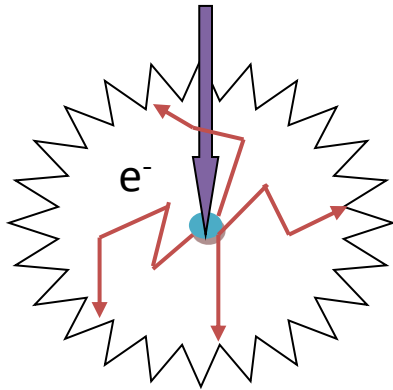
TWG Presentation
10/4/15



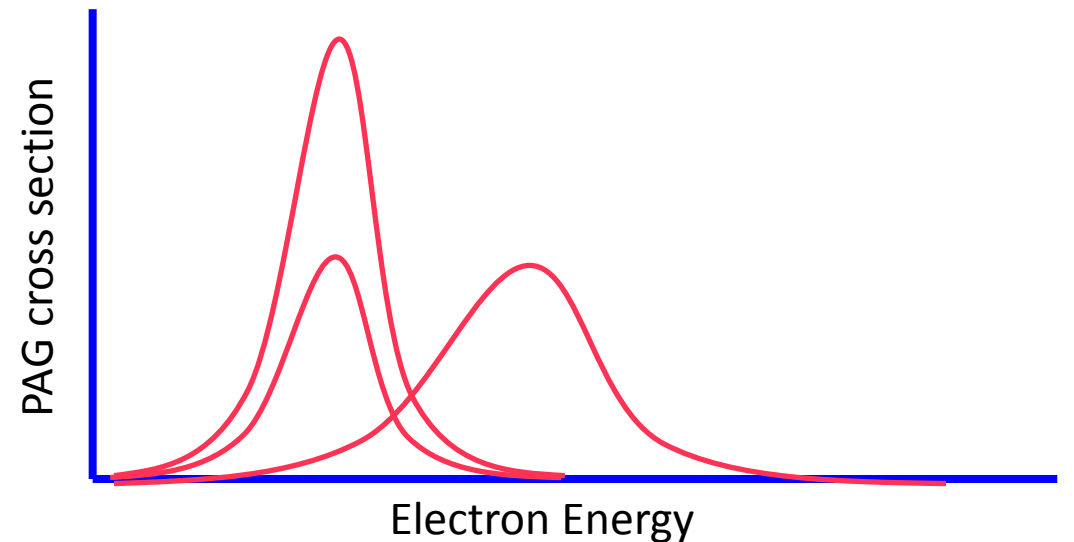
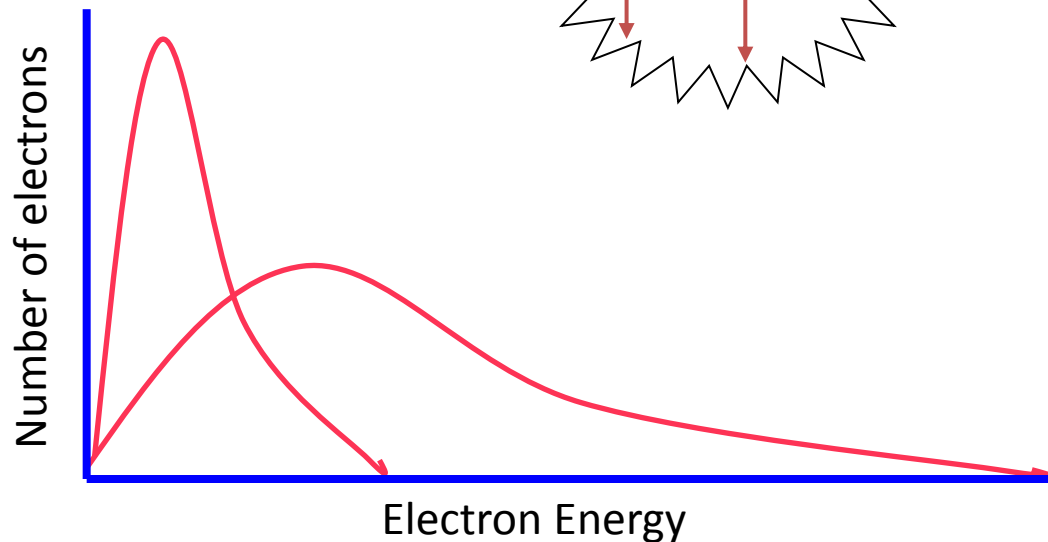
Accelerating the next technology revolution.

EUV Resist exposures are fundamentally secondary electron chemistry, not primarily photon chemistry

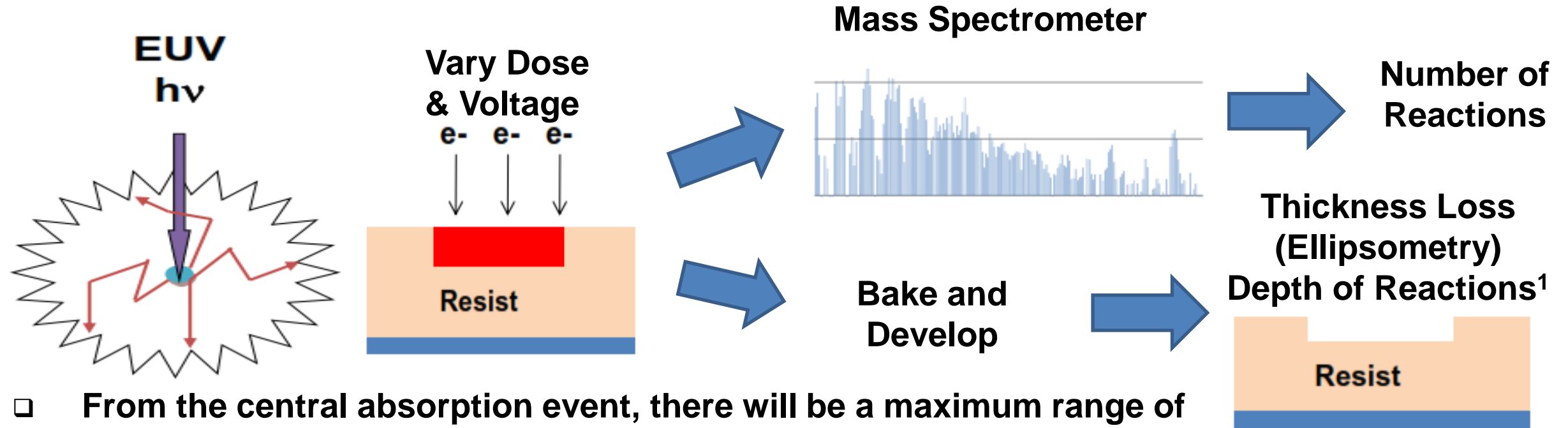
EUV
 $h\nu = 92 \text{ eV}$



Need to know the number and energy of electrons present in polymer
Need to know the cross section of the PAG to electrons
Larger overlap of electrons with PAG reactivity will be higher efficiency



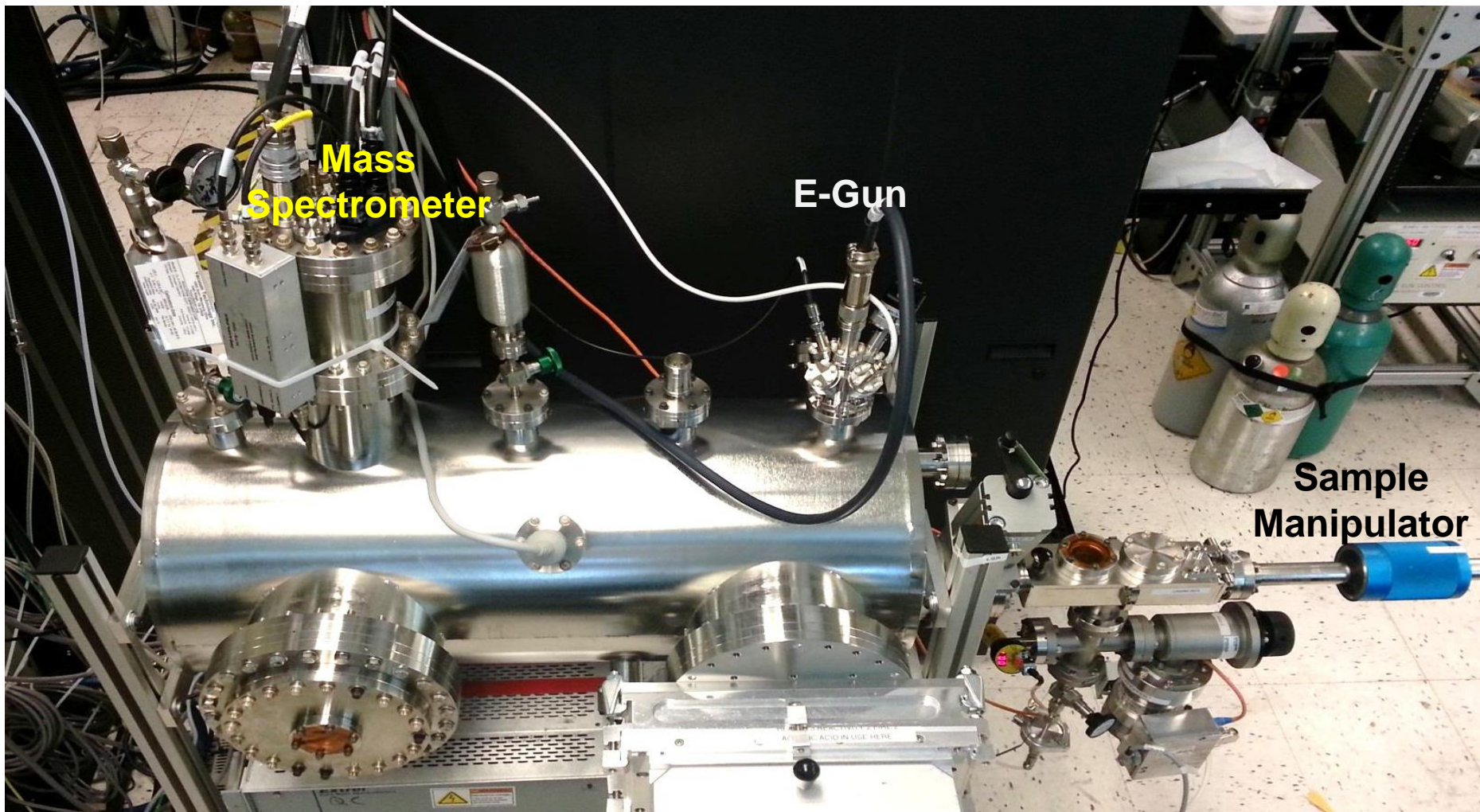
E-Beam Reaction Rate and Depth Studies



- From the central absorption event, there will be a maximum range of e^- movement
- We measure the range by top down exposures and measure the depth to represent the lateral electron travel away from the EUV absorption site
- We measure number of reactions by mass spectrometry

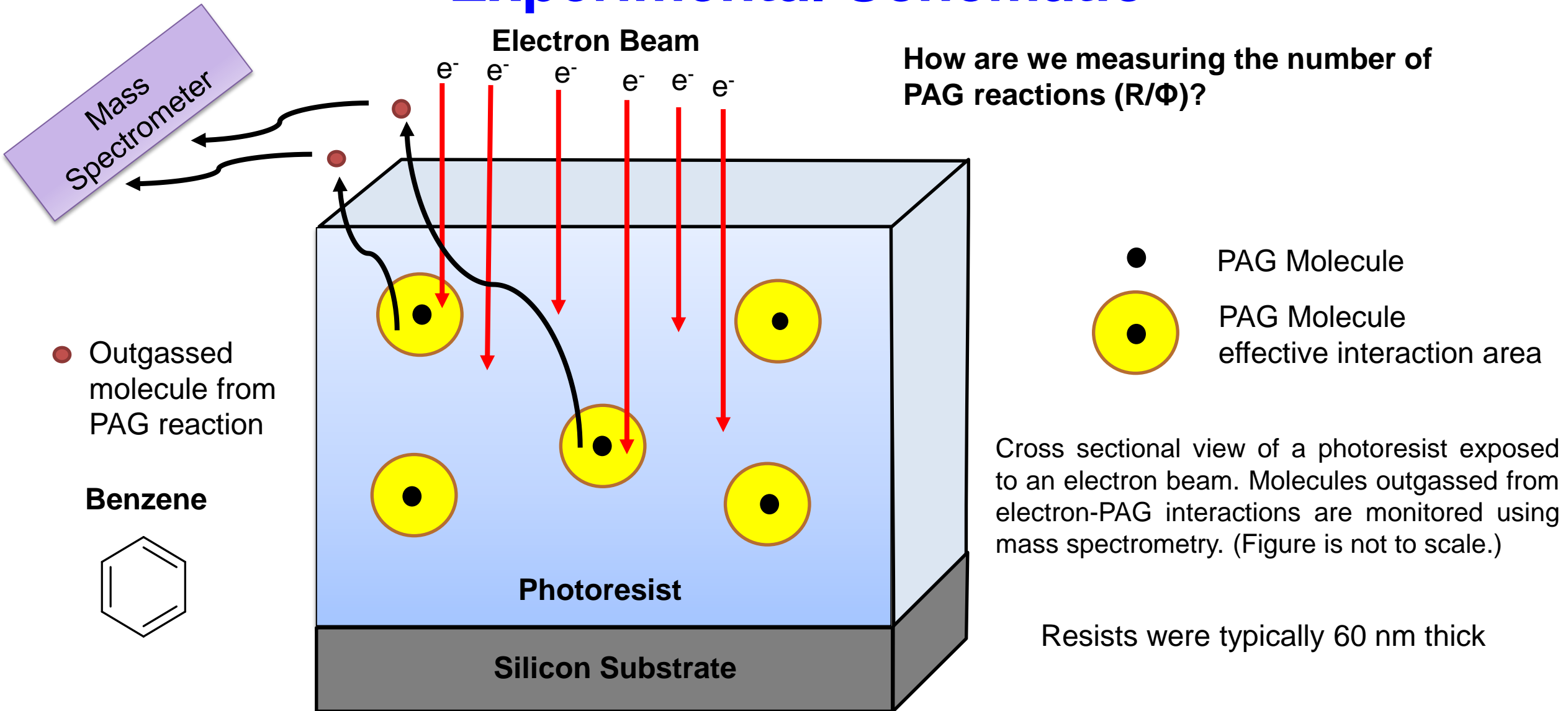
1. Amrit Narasimhan, Steven Grzeskowiak, Bharath Srivats, et al., "Studying secondary electron behavior in EUV resists using experimentation and modeling", Proceedings of SPIE Vol. 9422, 942208 (2015) SPIE Digital Library

Electron Resist Interaction Chamber (ERIC)



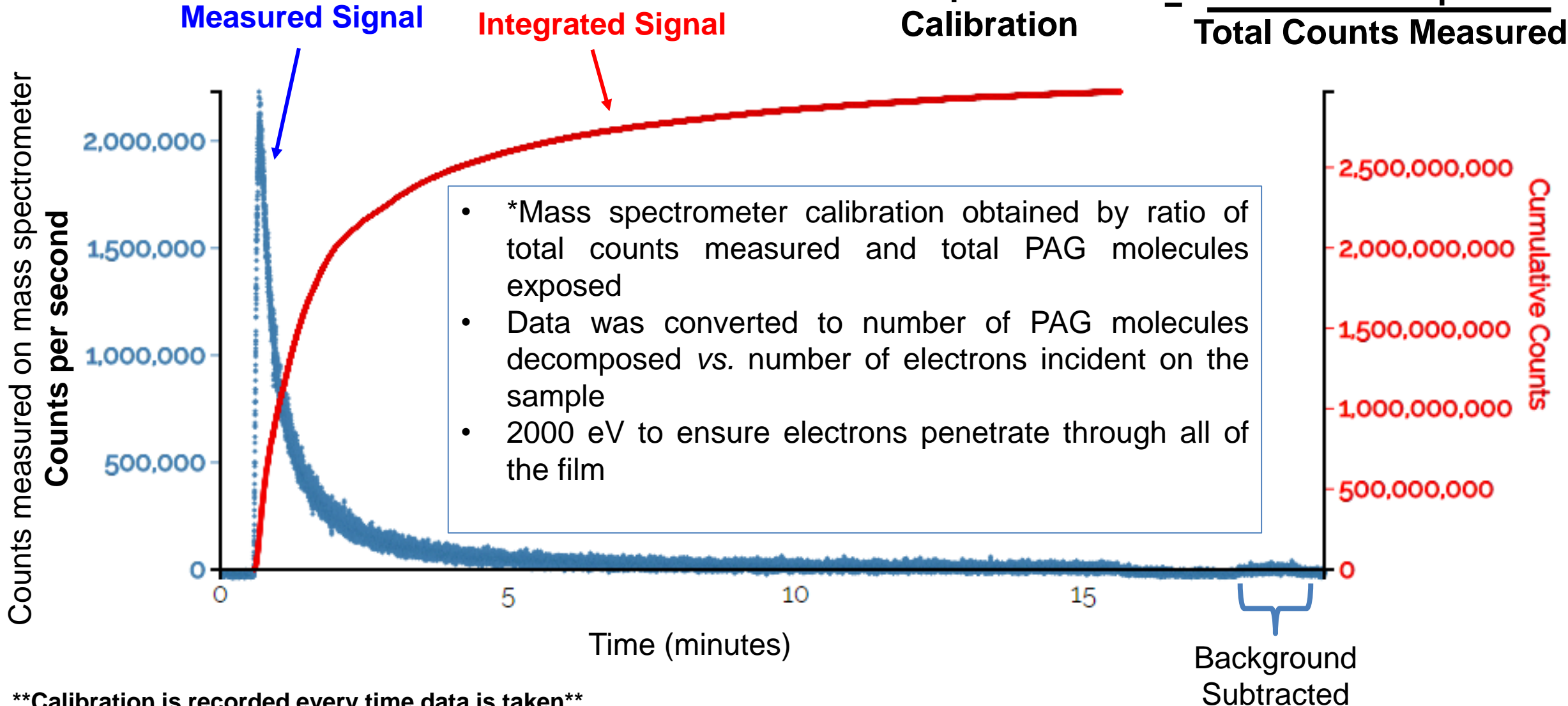
Expose EUV resist from 80-2000 eV across a wide range of doses and collect real-time outgassing information using mass spectrometry

Experimental Schematic



Calibration of Mass Spectrometer

$$\text{Mass Spectrometer Calibration} = \frac{\text{Total PAG exposed}}{\text{Total Counts Measured}}$$



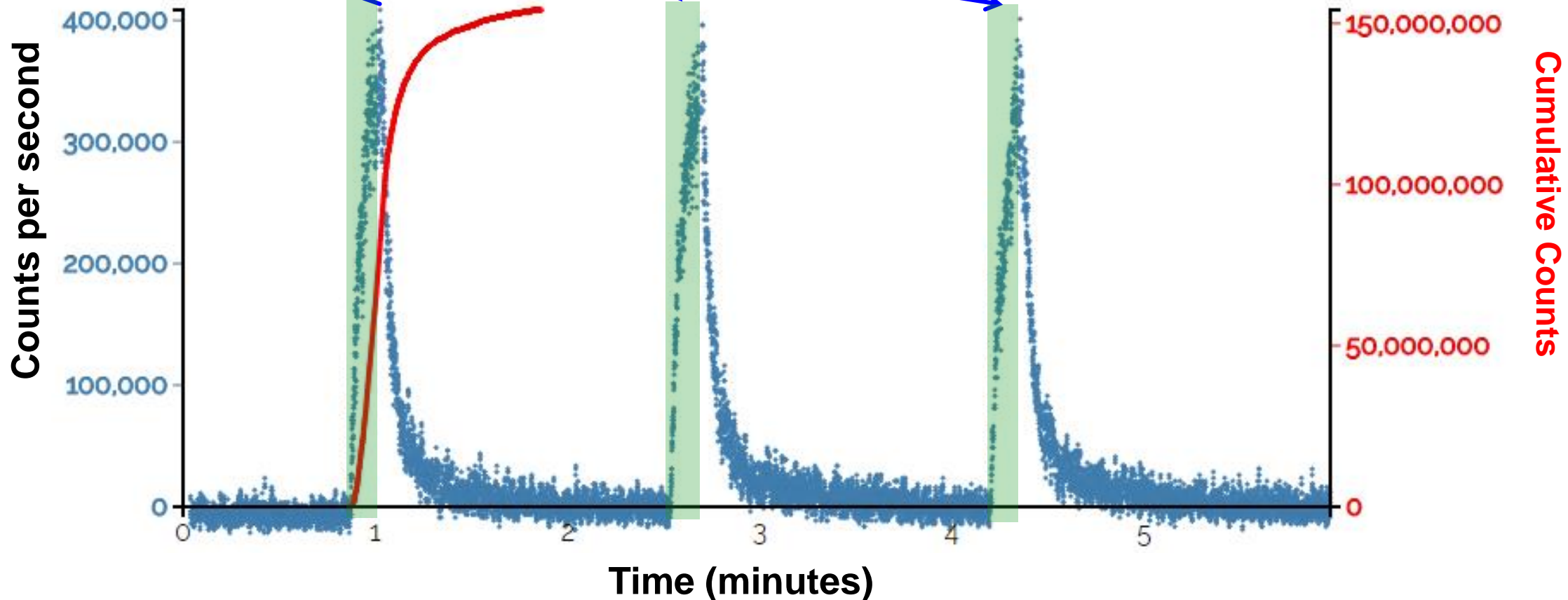
Calibration is recorded every time data is taken

Example of PAG Reaction Measurements

For improved accuracy, repeated measurements were performed with multiple smaller dose exposures, each providing number of PAG decompositions per electron after applying the calibration

Three 10 second exposures at ~ 50nA

Exposure Conditions are chosen such that the total dose upon the resist will be exposed in linear regime



Formulation (4 wt.% solids):

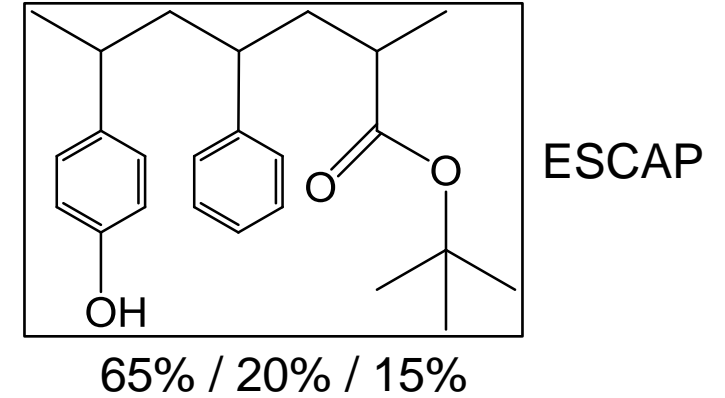
Resists Studied

83.5 wt.% Polymer

Spin Coat:
3700 RPM, 45s

Post Application Bake:
120 °C, 60s

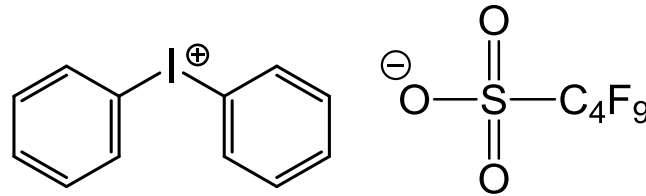
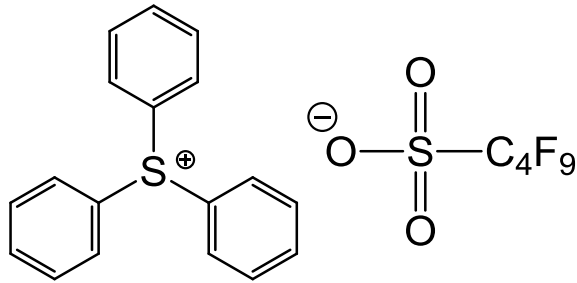
15 wt.% PAG



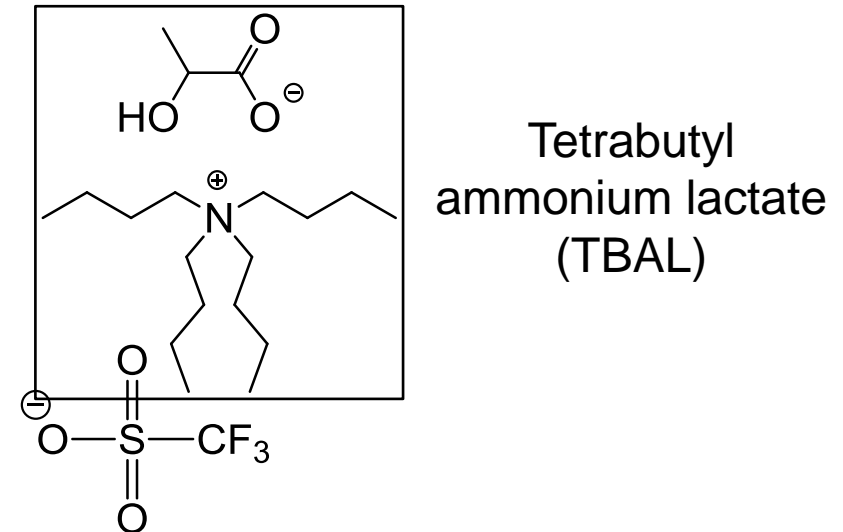
Triphenylsulfonium

Diphenyliodonium

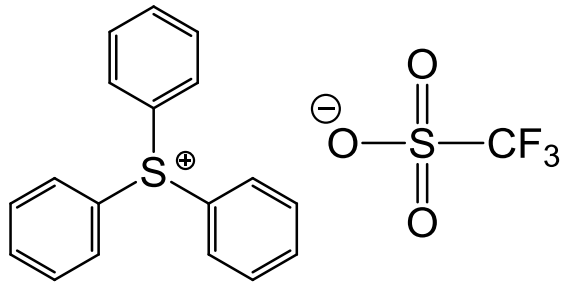
Nonaflate



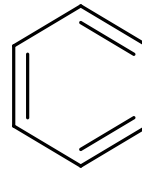
1.5 wt.% Base



Triflate

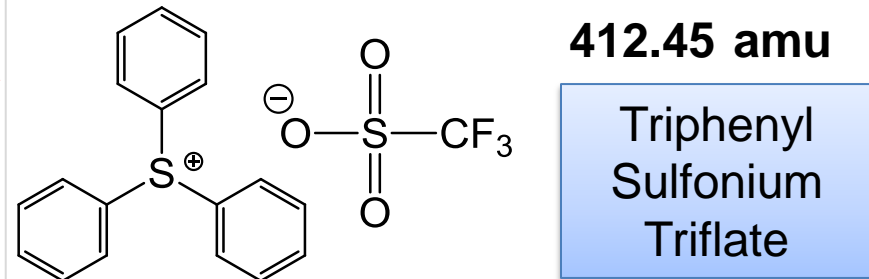
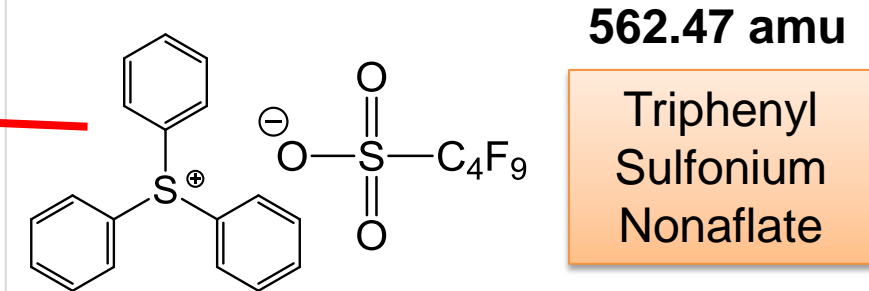
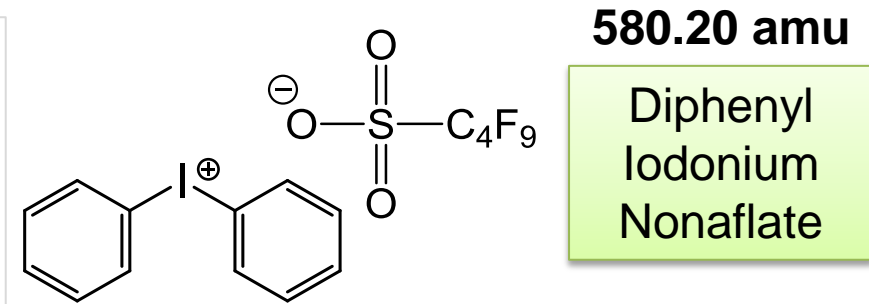
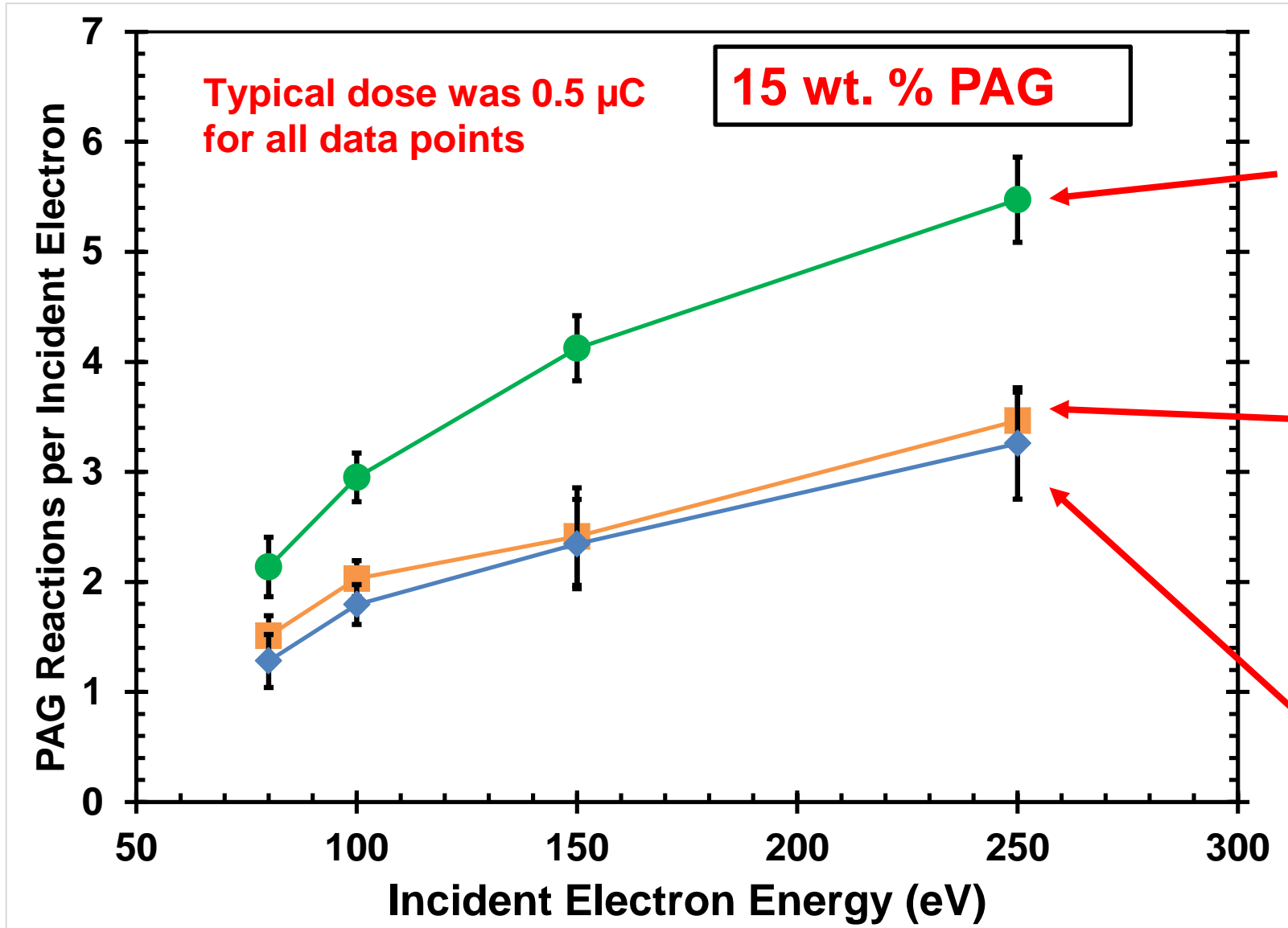


All 3 outgas benzene

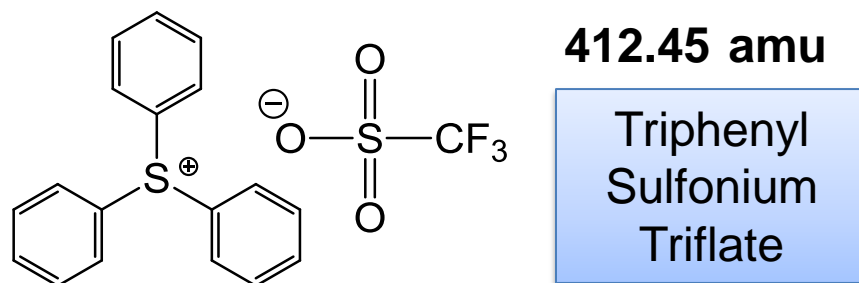
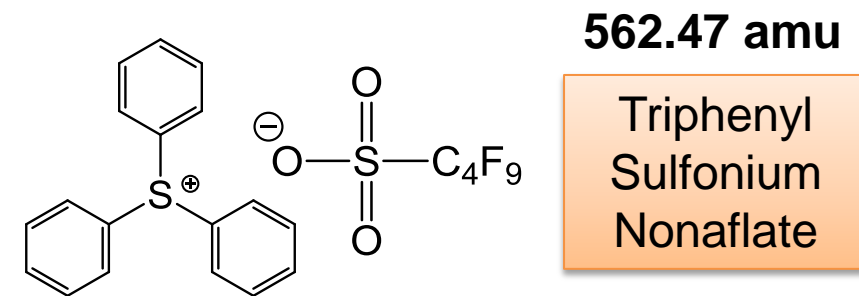
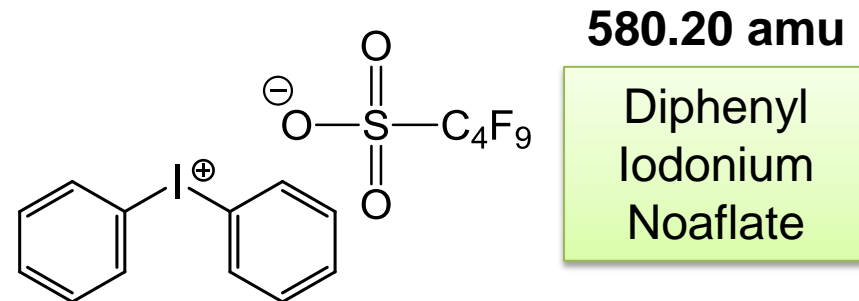
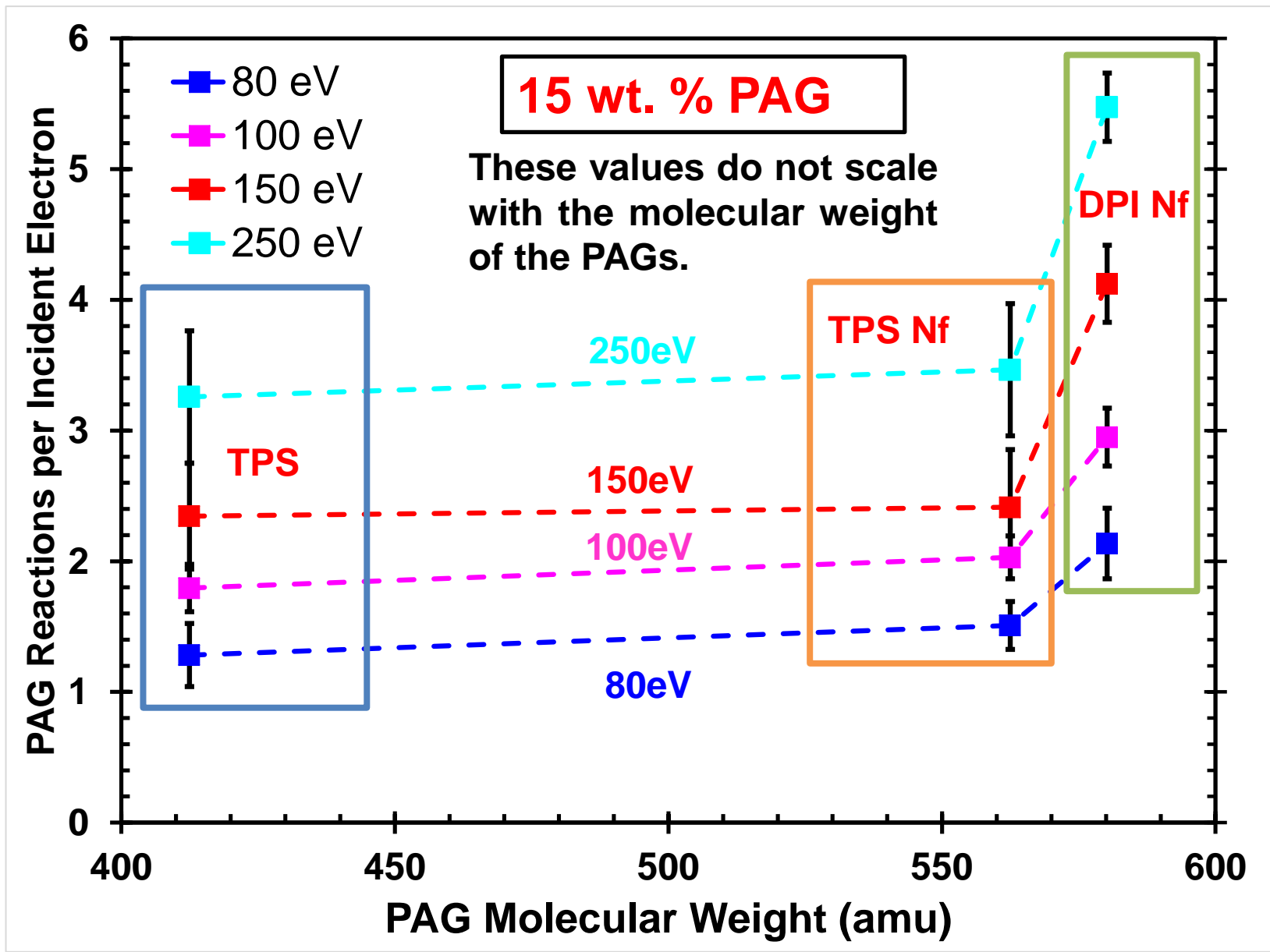


We chose three different PAGs,
and varied the cation and anion

PAG Reactions Per Incident Electron

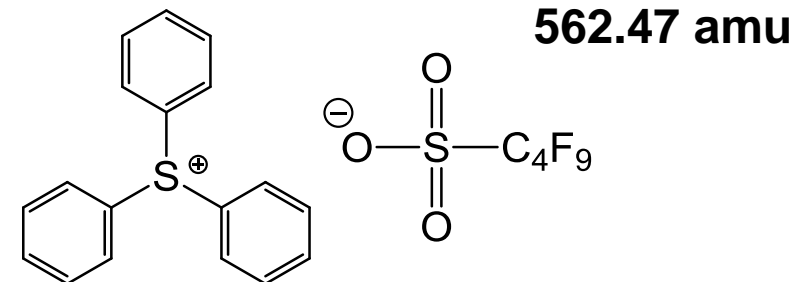
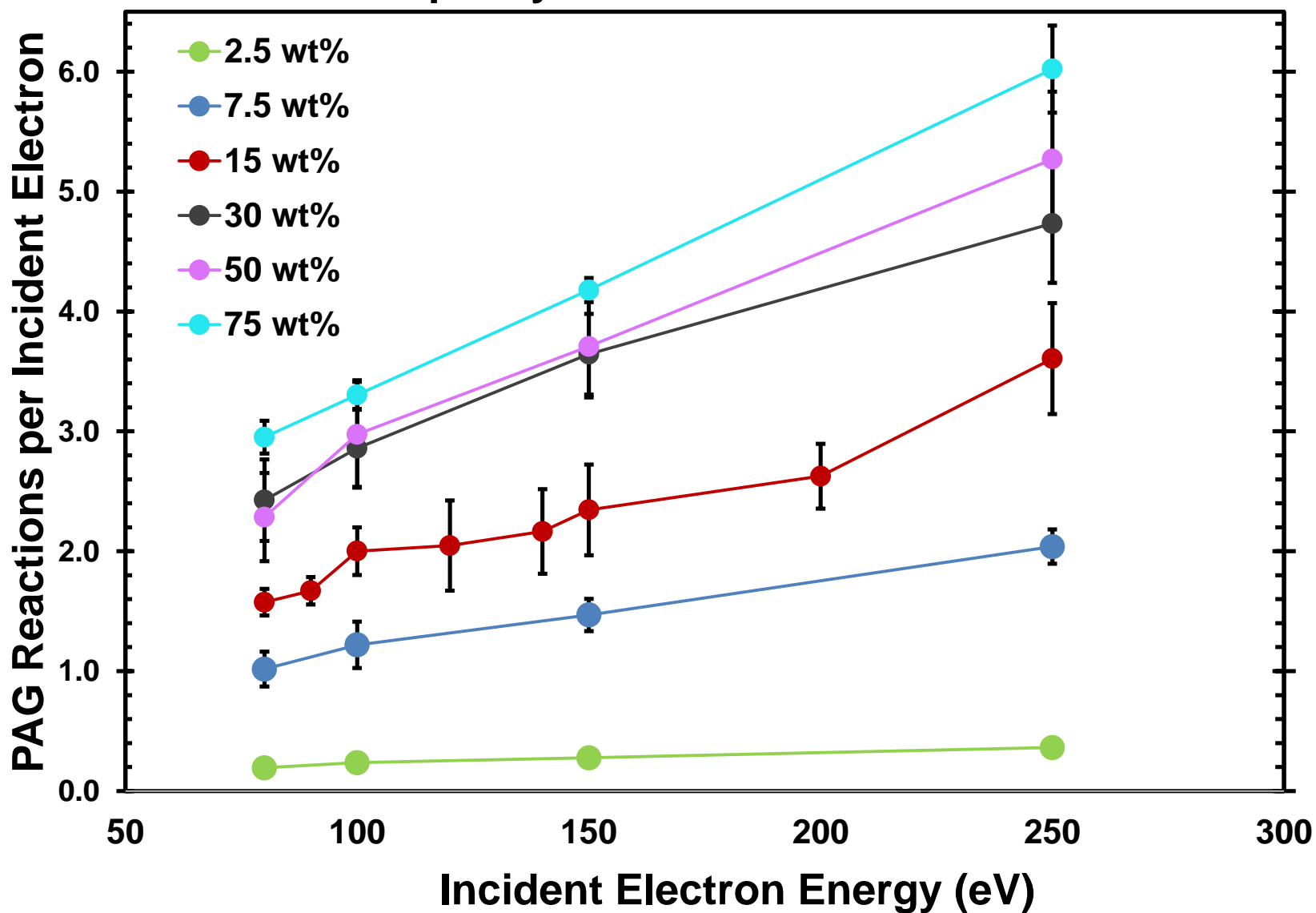


PAG Reactions per e⁻ vs. Molecular Weight



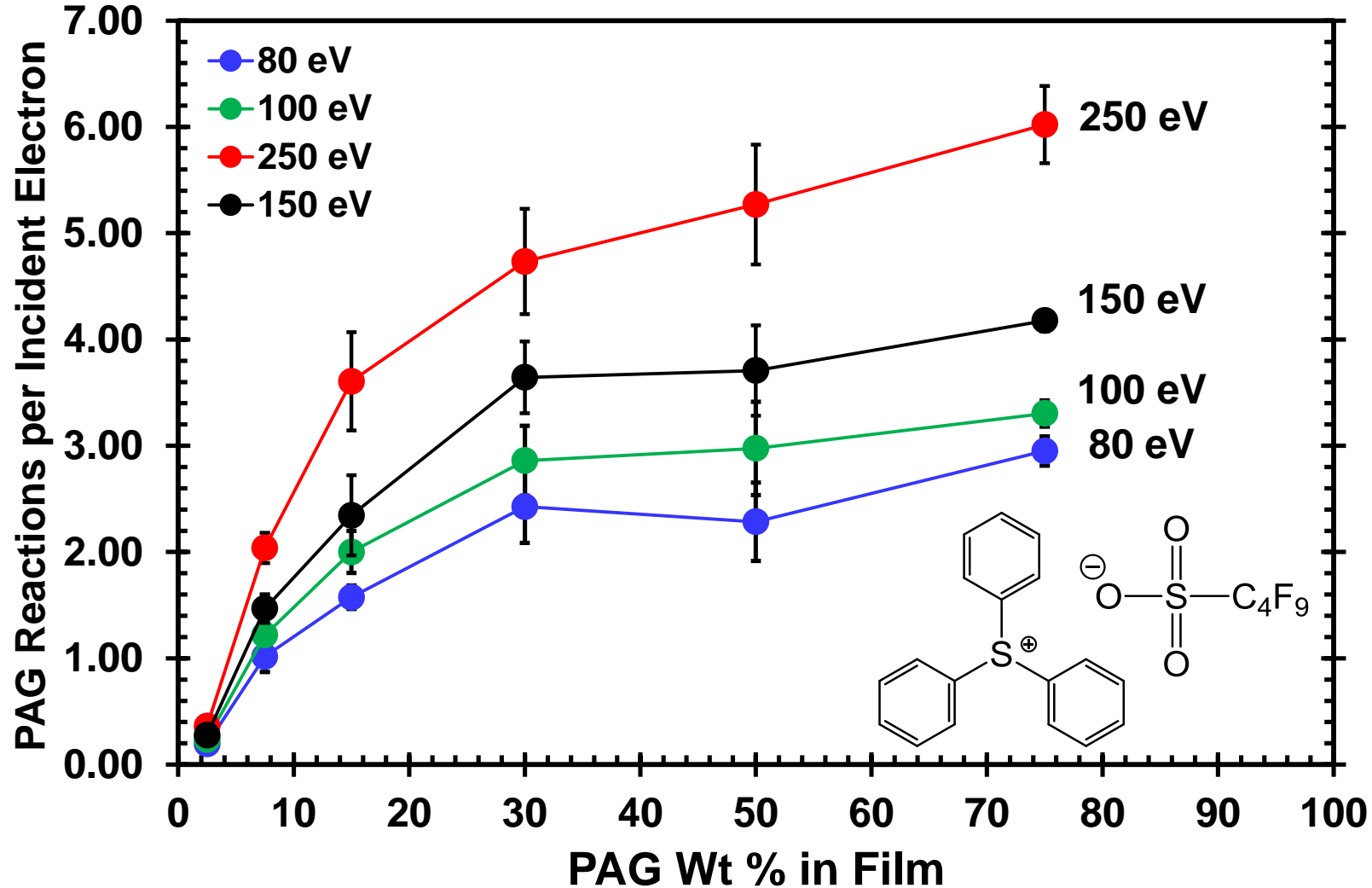
PAG Loading: Triphenylsulfonium Nonaflate

Triphenyl Sulfonium Nonaflate



PAG Loading: Triphenylsulfonium Nonaflate

Triphenylsulfonium Nonaflate



Acknowledgements

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Accelerating the next technology revolution.

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Supplying Polymers**

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